PG12NSSMB

Single Line TVS Diode for ESD Protection

Protection of Voltage Sensitive Components.

FEATURES

· Low profile package.

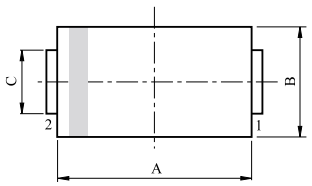
· Transient protection for data line to

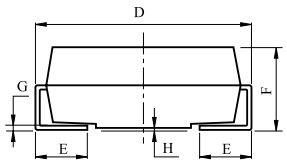
APPLICATIONS

· Devices for Unidirectional Applications.

· Automotive Controller.

· Notebooks, Desktops, & Servers.





DIM	MILLIMETERS
A	4.25 ~ 4.75
B	3.48 ~ 3.73
C	1.93 ~ 2.08
D	5.26 ~ 5.46
E	0.90 ~ 1.41
F	1.99 ~ 2.61
G	0.15 ~ 0.31
H	0.10 ~ 0.20

1. ANODE
2. CATHODE

SMB

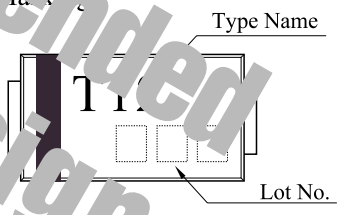
MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Pulse Power (tp=10/1000 μs)	P_{PK}		W
Peak Pulse Current (tp=10/1000 μs)	I_{PP}		A
Operating Temperature	T_j	-55 150	℃
Storage Temperature	T_{stg}	55 150	℃

* Notes) : (1) Derated above Ta=25℃ per power derating curve

(2) Mounted on 0.2×0.2 (5.0×5.0㎜) copper pads to each terminal.

(3) Mounted on minimum recommened pad lay out

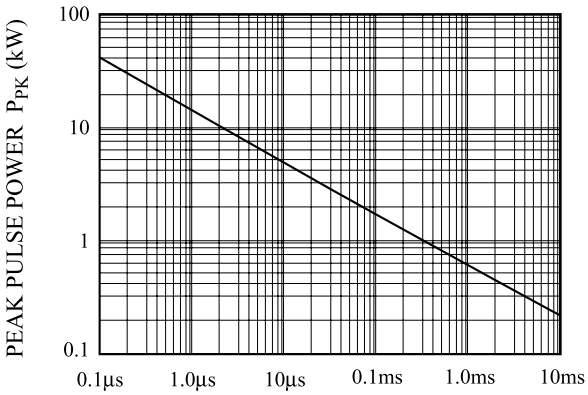


Not recommended for new design

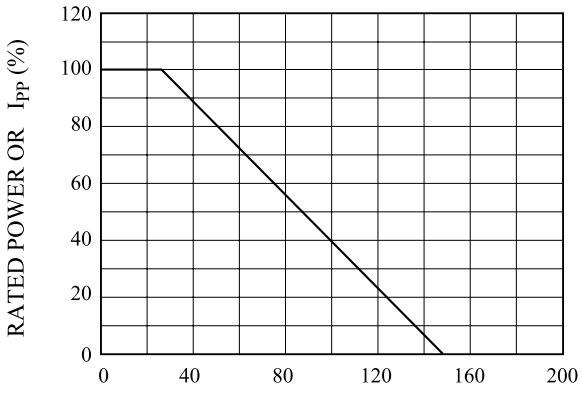
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	12	V
Reverse Breakdown Voltage	V_{BR}	I_t=1.0mA	13.3	-	14.7	V
Reverse Leakage Current	I_R	V_{RWM}=12V	-	-	5.0	μA
Clamping Voltage	V_C	I_{PP}=30.2A, tp=10/1000 μs	-	-	19.9	V

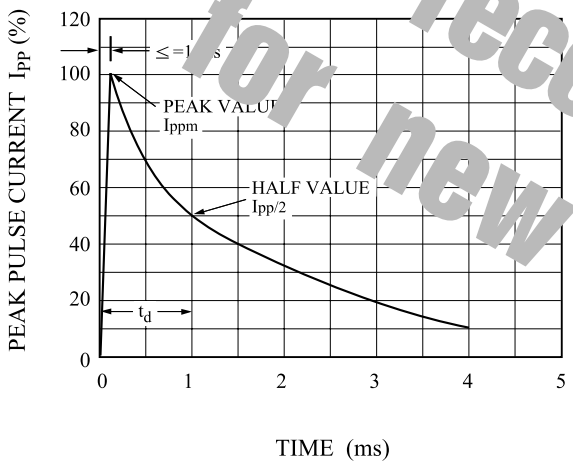
NON-REPETITIVE PEAK PULSE POWER vs. PULSE TIME



POWER DERATION CURVE



PULSE WAVEFORM



Not recommended for new design